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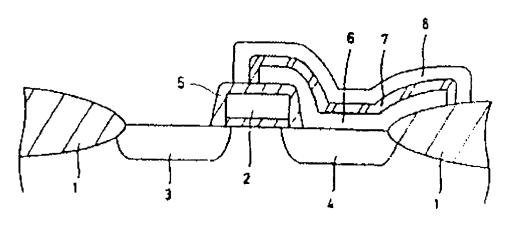
MANUFACTURE THEREOF CONDUCTOR LAYER AND CAPACITOR USING (54) CONDUCTOR LAYER,

(57) Abstract:

capacitor using said layer wherein electric field does not concentrate and amorphous silicon containing no crystal grains. forming the conductor layer by using dielectric strength is increased, by PURPOSE: To obtain a conductor layer whose surface is flat, and a

above gas, and its temperature is as growth is performed by heating the oxygen is used as reaction gas. Vapor disilane or trisilane or tetrasilane and of tetrasilane. Thus a flat surface disilane, 350-450°C in the case of CONSTITUTION: Mixed gas of quality is formed on a substrate. By amorphous silicon layer of excellent conductor layer composed of an trisilane, and 300-400°C in the case polycrystalline silicon layer is region on the amorphous layer 6. eliminated from the region except a an insulating layer 7 is formed, it is region in contact with drain 4. After eliminated from the region except a is subjected to vapor growth on a using the above manufacturing follows; 400-500°C in the case of conducting layer 8 is formed. layer 6, the insulating layer 7 and the composed of the amorphous silicon insulating layer 7, and a capacitor region except a region on the formed, it is eliminated from the After a conductor layer 8 like a MOS field effect transistor, and method, an amorphous silicon layer 6

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